

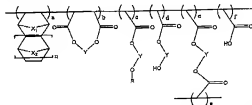
In the Claims:

Please cancel claims 4-7 and 14-21 without prejudice or disclaimer.

Please amend claim 1 as follows:

Claim 1 (currently amended) A photoresist polymer comprising a repeating unit of following formula 1:

Formula 1



wherein, X_1 and X_2 are independently selected from the group consisting of CH_2 , CH_2CH_2 , O and S;

Y is C_1 - C_{10} alkylene or alkylene comprising an ether linkage;

R is an acid labile protecting group;

n is an integer from 0 to 2; and

a : b : c : d : e : f is 20-40mol% : 4- present in an amount between 0 and 20mol% : 20-70mol% : 4- present in an amount between 0 and 30mol% : 1 present in an amount up between 0 and 20mol% : 0-20mol%.

Claim 2 (original) The photoresist polymer according to claim 1, wherein the acid labile protecting group is selected from the group consisting of tert-butyl, tetrahydropyran-2-yl, 2-methyl tetrahydropyran-2-yl, tetrahydrofuran-2-yl, 2-methyl tetrahydrofuran-2-yl, 1-methoxypropyl, 1-methoxy-1-methylethyl, 1-ethoxypropyl, 1-ethoxy-1-methylethyl, 1-methoxyethyl, 1-ethoxyethyl, tert-butoxyethyl, 1-isobutoxyethyl and 2-acetylmethyl-1-yl.

Claim 3 (original) The photoresist polymer according to claim 1, wherein n is 0, X_1 is CH_2 , Y is CH_2CH_2 or $\text{CH}_2\text{CH}_2\text{OCH}_2\text{CH}_2$, and R is tert-butyl.

Claims 4-7 (currently canceled)

Claim 8 (original) A photoresist composition comprising (i) the photoresist polymer of claim 1, (ii) a photoacid generator; and (iii) an organic solvent.

Claim 9 (original) The photoresist composition according to claim 8, wherein the photoacid generator is selected from the group consisting of phthalimidotrifluoromethane sulfonate, dinitrobenzyltosylate, n-decyl disulfone, naphthylimido trifluoromethane sulfonate and mixture thereof.

Claim 10 (original) The photoresist composition according to claim 9, wherein the photoacid generator is selected from the group consisting of diphenyl iodide hexafluorophosphate, diphenyl iodide hexafluoroarsenate, diphenyl iodide hexafluoroantimonate, diphenyl p-methoxyphenyl triflate, diphenyl p-toluenyl triflate, diphenyl p-isobutylphenyl triflate, diphenyl p-tert-butylphenyl triflate, triphenylsulfonium hexafluorophosphate, triphenylsulfonium hexafluoroarsenate, triphenylsulfonium hexafluoroantimonate, triphenylsulfonium triflate, dibutyl-naphthylsulfonium triflate and mixture thereof.

Claim 11 (original) The photoresist composition according to claim 8, wherein the photoacid generator is present in an amount ranging from about 0.1 to about 10% by weight of the photoresist polymer.

Claim 12 (original) The photoresist composition according to claim 8, wherein the organic solvent is selected from the group consisting of ethyl 3-ethoxypropionate, methyl 3-methoxypropionate, cyclohexanone, propyleneglycol methyl ether acetate, n-heptanone, ethyl lactate and mixture thereof.

Claim 13 (original) The photoresist composition according to claim 8, wherein an amount of organic solvent ranges from about 300% to about 1500% by weight of the photoresist polymer.

Claims 14-21 (currently canceled)